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Attorney Docket No. 5308-156

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Ryu et al.
Application Serial No.: 09/911,995
Filed: July 24, 2001
For: *Silicon Carbide Power Metal-Oxide Semiconductor Field Effect Transistors Having A Shorting Channel and Methods of Fabricating Silicon Carbide Metal-Oxide Semiconductor Field Effect Transistors Having a Shorting Channel*

U.S. Patent No.: 6,956,238 B2
Issued: October 18, 2005

Date: March 16, 2006

Commissioner for Patents
Attn: Certificate of Correction Branch
P.O. Box 1450
Alexandria, VA 22313-1450

REQUEST FOR ENTRY OF CERTIFICATE OF CORRECTION UNDER 35 U.S.C §254 AND 37 C.F.R. §1.322

Sir:

The Assignee of record for the above-referenced patent hereby requests, pursuant to 35 U.S.C §254 and 37 C.F.R. §1.322, that a Certificate of Correction be issued. This request is made in order to correct the mistakes incurred through the fault of the U.S. Patent and Trademark Office. No fee is believed due. However, the Commissioner is authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

The mistakes appearing in the patent are set forth with corrections on the Certificate of Correction enclosed herewith, with an additional copy thereof and a return post card.

Respectfully submitted,

Elizabeth A. Stanek
Registration No. 48,568

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Certificate of Mailing under 37 CFR 1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, Attn: Certificate of Correction Branch, P.O. Box 1450, Alexandria, VA 22313-1450 on March 16, 2006.

/Monica L Croom/
Monica L. Croom

PTO/SB/44 (04-04)
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INVENTOR(S) : Ryu et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the Title Page,
Section 60 should include -- Application No. 09/834,283, filed on Apr. 12, 2001, now Pat. No. 6,610,366. --

Section 56 should include the following references:
Under U.S. PATENT DOCUMENTS

6,767,843	07/2004	Lipkin et al.	438/758
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